

Silicon N-Channel Power MOSFET

General Description :

GL20N65A8, the silicon N-channel Enhanced VDMOSFET, is obtained by the self-aligned planar Technology which reduce the conduction loss, improve switching performance and enhance the avalanche energy. The transistor can be used in various power switching circuit for system miniaturization and higher efficiency. The package form is TO-220AB, which accords with the RoHS standard.

Features :

- Fast Switching
- Low ON Resistance($R_{ds(on)} \leq 0.35\Omega$)
- Low Gate Charge (Typical Data: 53nC)
- Low Reverse transfer capacitances(Typical: 14.3pF)
- 100% Single Pulse avalanche energy Test

Applications:

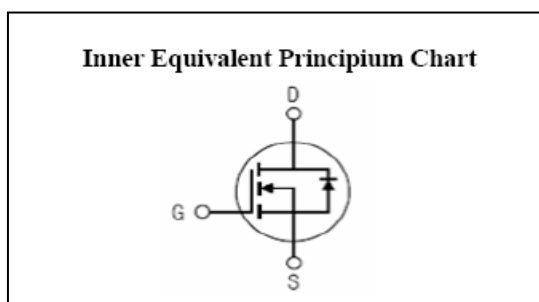
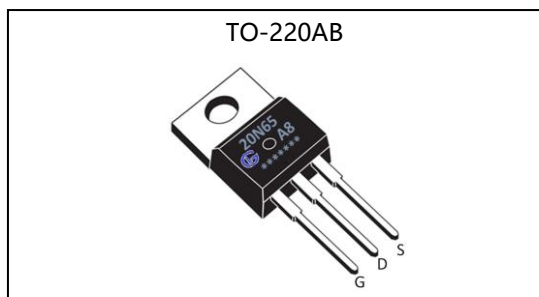
- Power switch circuit of adaptor and charger

Absolute ($T_c=25^\circ\text{C}$ unless otherwise specified) :

Symbol	Parameter	Rating	Units
V_{DSS}	Drain-to-Source Voltage	650	V
I_D	Continuous Drain Current	20	A
	Continuous Drain Current $T_c=100^\circ\text{C}$	14	A
I_{DM}^{a1}	Pulsed Drain Current	80	A
V_{GS}	Gate-to-Source Voltage	± 30	V
E_{AS}^{a2}	Single Pulse Avalanche Energy	2564	mJ
E_{AR}^{a1}	Avalanche Energy ,Repetitive	100	mJ
I_{AR}^{a1}	Avalanche Current	4.5	A
dv/dt^{a3}	Peak Diode Recovery dv/dt	5.0	V/ns
P_D	Power Dissipation	250	W
	Derating Factor above 25°C	2.0	W/ $^\circ\text{C}$
T_J, T_{stg}	Operating Junction and Storage Temperature Range	150 , -55 to 150	$^\circ\text{C}$
T_L	Maximum Temperature for Soldering	300	$^\circ\text{C}$

Caution Stresses greater than those in the "Absolute Maximum Ratings" may cause permanent damage to the device

V_{DSS}	650	V
I_D	20	A
$P_D(T_c=25^\circ\text{C})$	250	W
$R_{DS(ON).TYP.}$	0.32	Ω





GL20N65A8

无锡光磊电子科技有限公司

Silicon N-Channel Power MOSFET

Thermal Characteristics

Symbol	Parameter	Rating	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	0.5	$^{\circ}\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	62	$^{\circ}\text{C}/\text{W}$

Electrical Characteristics ($T_c = 25^{\circ}\text{C}$ unless otherwise specified) :

OFF Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
V_{DSS}	Drain to Source Breakdown Voltage	$V_{GS}=0\text{V}, I_D=250\mu\text{A}$	650	--	--	V
$\Delta V_{DSS}/\Delta T_J$	Bvdss Temperature Coefficient	$I_D=250\mu\text{A}, \text{Reference } 25^{\circ}\text{C}$	--	0.65	--	$\text{V}/^{\circ}\text{C}$
I_{DSS}	Drain to Source Leakage Current	$V_{DS}=650\text{V}, V_{GS}=0\text{V}, T_a=25^{\circ}\text{C}$	--	--	1.0	μA
		$V_{DS}=520\text{V}, V_{GS}=0\text{V}, T_a=125^{\circ}\text{C}$	--	--	100	
$I_{GSS(F)}$	Gate to Source Forward Leakage	$V_{GS}=+30\text{V}$	--	--	100	nA
$I_{GSS(R)}$	Gate to Source Reverse Leakage	$V_{GS}=-30\text{V}$	--	--	-100	nA

ON Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
$R_{DS(ON)}$	Drain-to-Source On-Resistance	$V_{GS}=10\text{V}, I_D=10\text{A}$	--	0.32	0.35	Ω
$V_{GS(TH)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	2.0	--	4.0	V
g_{fs}	Forward Trans conductance	$V_{DS}=15\text{V}, I_D=10\text{A}$	--	17	--	S
Pulse width < 380 μs ; duty cycle < 2%.						

Dynamic Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
C_{iss}	Input Capacitance	$V_{GS}=0\text{V}, V_{DS}=25\text{V}$ $f=1.0\text{MHz}$	--	2850	--	pF
C_{oss}	Output Capacitance		--	225	--	
C_{rss}	Reverse Transfer Capacitance		--	14.3	--	

Resistive Switching Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
$t_{d(ON)}$	Turn-on Delay Time	$I_D=20\text{A}, V_{DD}=300\text{V}$ $R_g=25\Omega$	--	36	--	ns
t_r	Rise Time		--	73	--	
$t_{d(OFF)}$	Turn-Off Delay Time		--	166	--	
t_f	Fall Time		--	73	--	
Q_g	Total Gate Charge	$I_D=20\text{A}, V_{DD}=300\text{V}$ $V_{GS}=10\text{V}$	--	53	--	nC
Q_{gs}	Gate to Source Charge		--	15.5	--	
Q_{gd}	Gate to Drain ("Miller") Charge		--	10.3	--	



GL20N65A8

无锡光磊电子科技有限公司

Silicon N-Channel Power MOSFET

Source-Drain Diode Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
I_{SD}	Continuous Source Current (Body Diode)		--	--	20	A
I_{SM}	Maximum Pulsed Current (Body Diode)		--	--	80	A
V_{SD}	Diode Forward Voltage	$I_S=12A, V_{GS}=0V$	--	--	1.5	V
t_{rr}	Reverse Recovery Time	$I_S=12A, T_J=25^{\circ}C$	--	585	--	ns
Q_{rr}	Reverse Recovery Charge	$di_F/dt=100A/\mu s, V_{GS}=0V$	--	2.9	--	μC

a1 : Repetitive rating; pulse width limited by maximum junction temperature

a2 : $L=10mH, I_D=15.5A$, Start $T_J=25^{\circ}C$

a3 : $I_{SD}=20A, di/dt \leq 100A/\mu s, V_{DD} \leq BV_{DS}$, Start $T_J=25^{\circ}C$

Characteristics Curve :

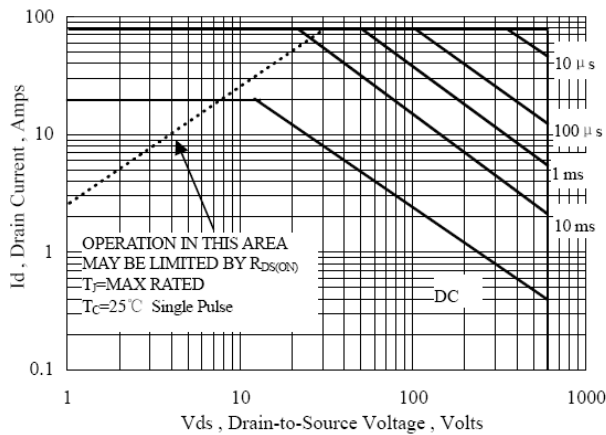


Figure 1 Maximum Forward Bias Safe Operating Area

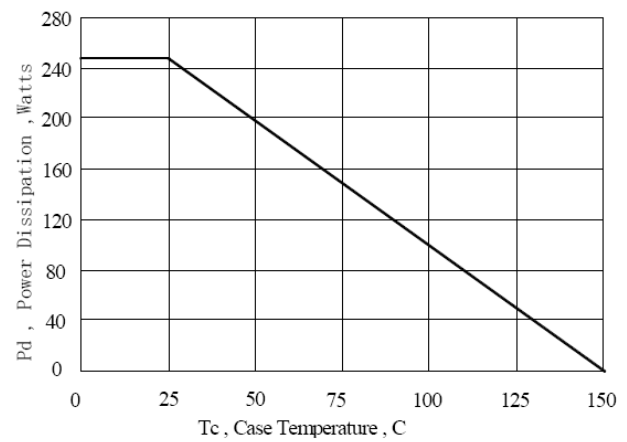


Figure 2 Maximum Power Dissipation vs Case Temperature

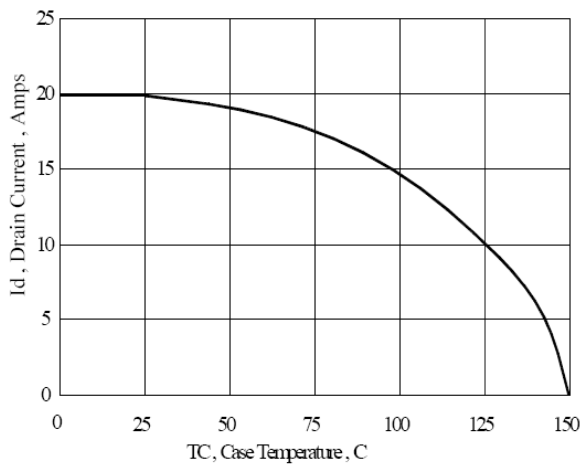


Figure 3 Maximum Continuous Drain Current vs Case Temperature

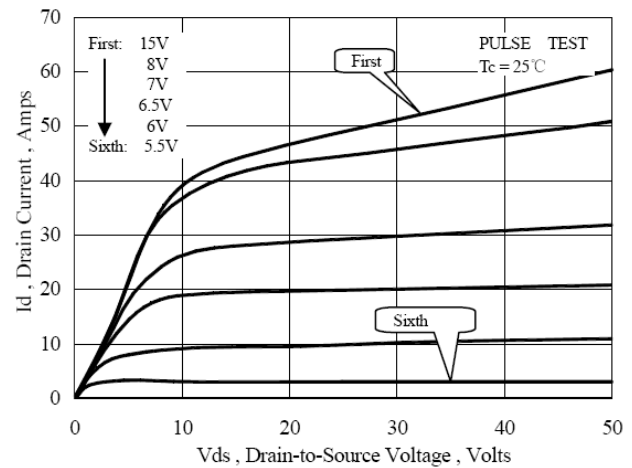


Figure 4 Typical Output Characteristics

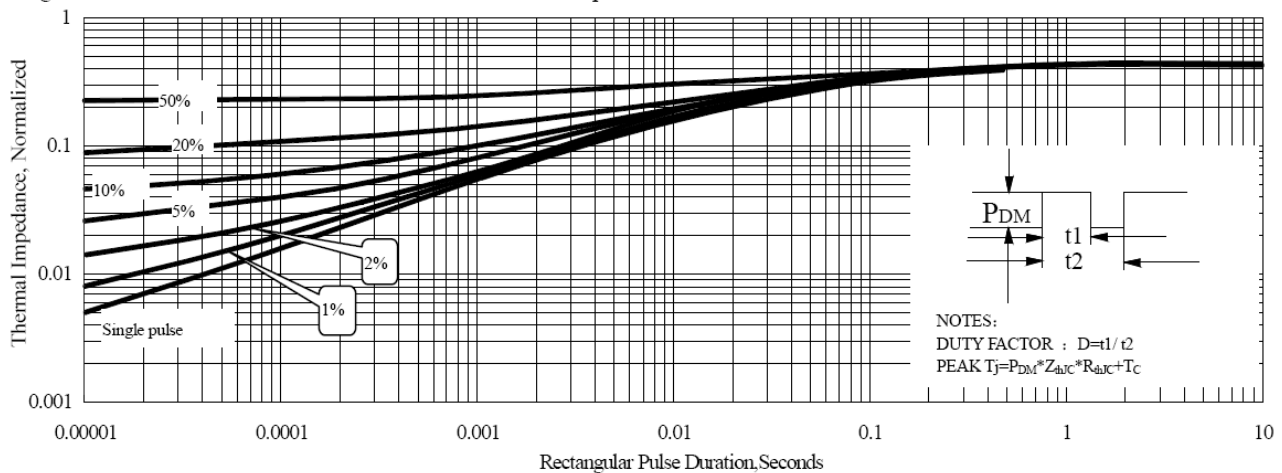


Figure 5 Maximum Effective Thermal Impedance, Junction to Case

Silicon N-Channel Power MOSFET

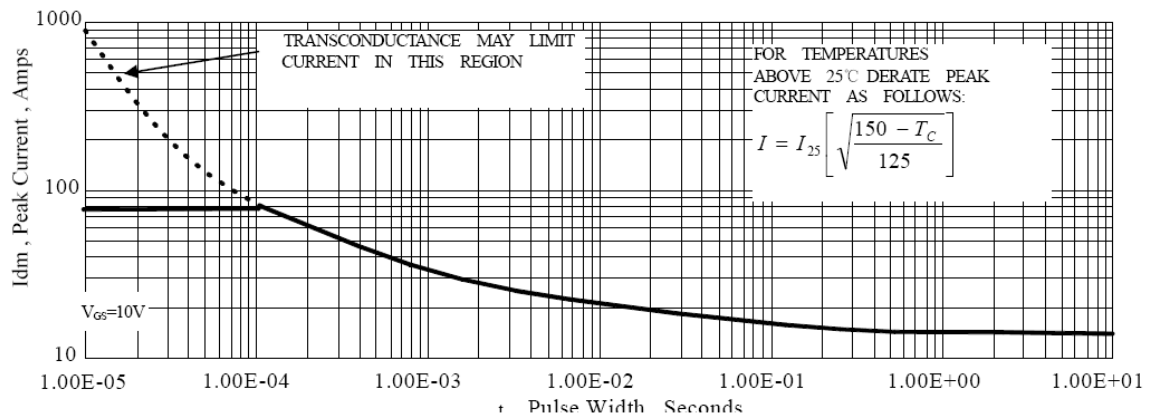


Figure 6 Maximum Peak Current Capability

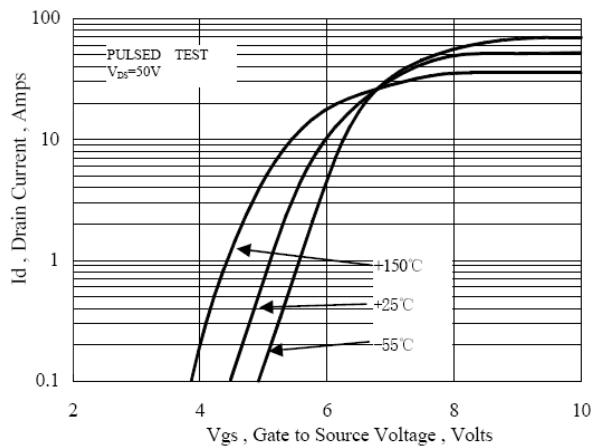


Figure 7 Typical Transfer Characteristics

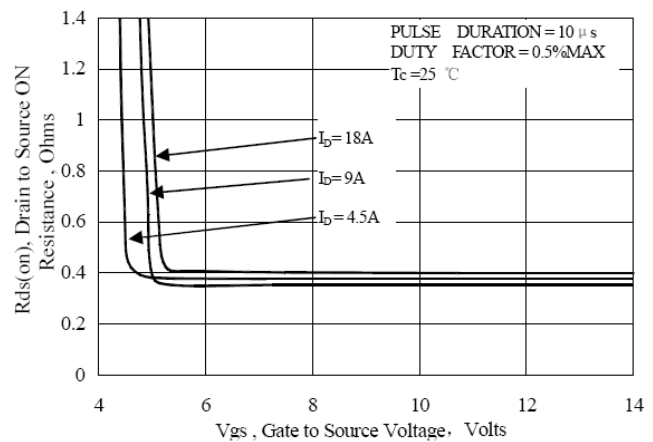


Figure 8 Typical Drain to Source ON Resistance vs. Gate Voltage and Drain Current

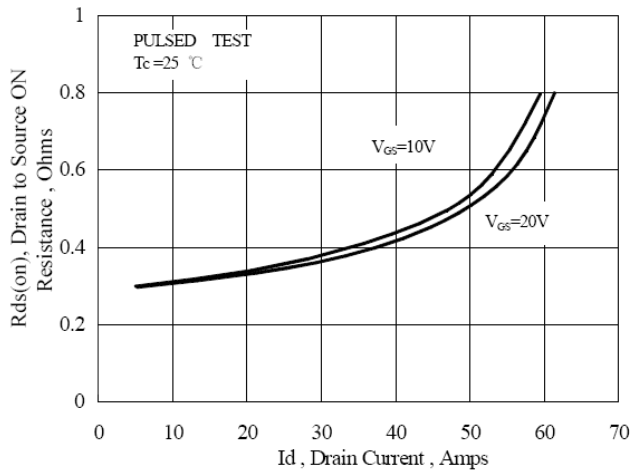


Figure 9 Typical Drain to Source ON Resistance vs. Drain Current

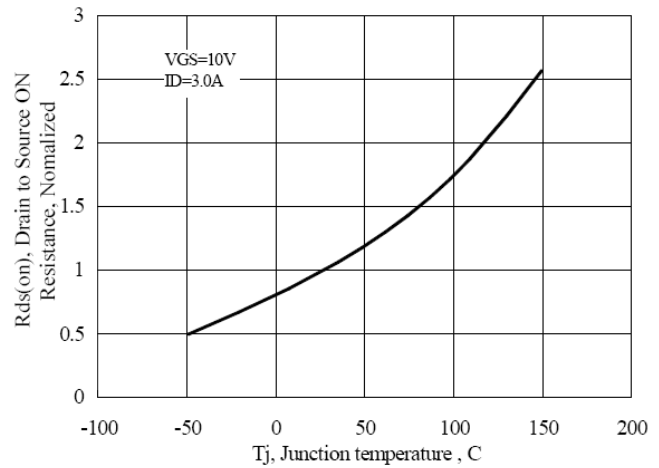


Figure 10 Typical Drain to Source on Resistance vs. Junction Temperature



GL20N65A8

无锡光磊电子科技有限公司

Silicon N-Channel Power MOSFET

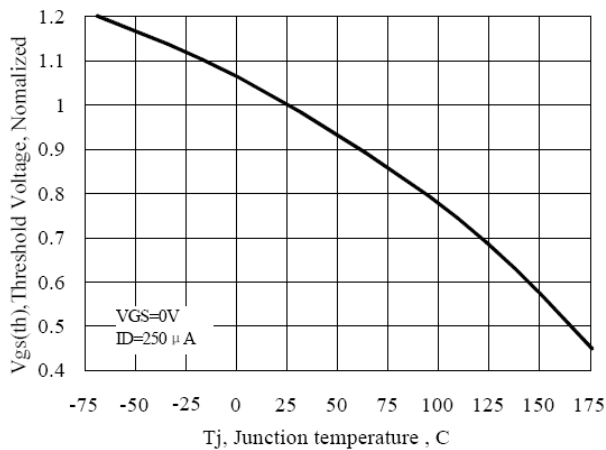


Figure 11 Typical Theshold Voltage vs Junction Temperature

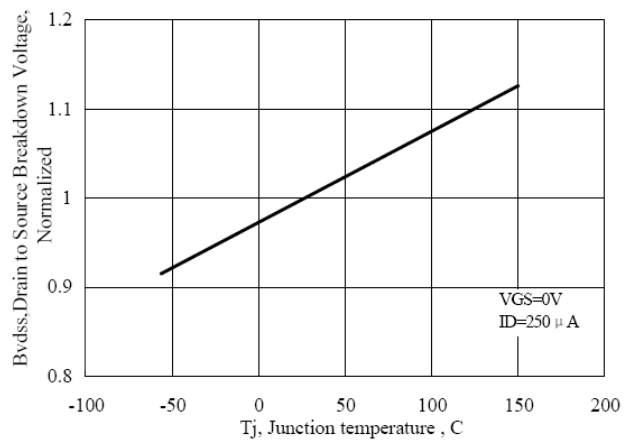


Figure 12 Typical Breakdown Voltage vs Junction Temperature

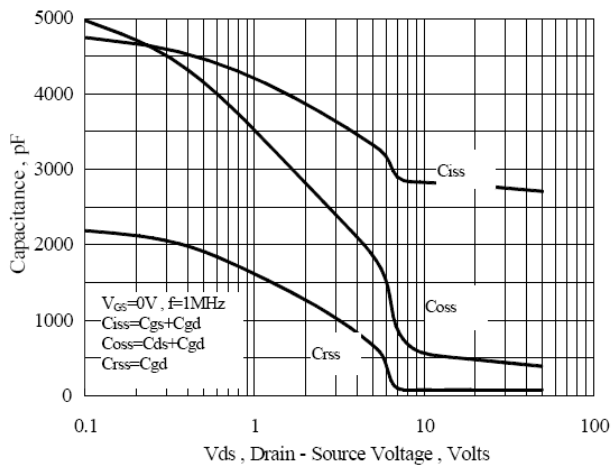


Figure 13 Typical Capacitance vs Drain to Source Voltage

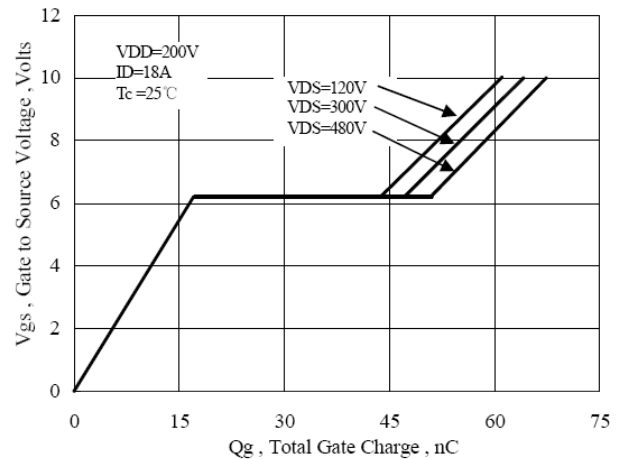


Figure 14 Typical Gate Charge vs Gate to Source Voltage

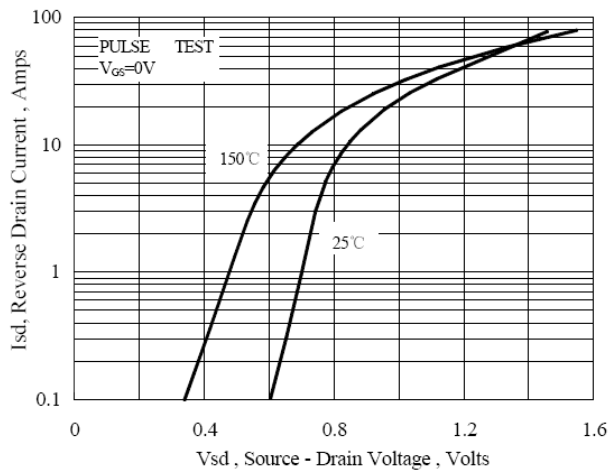


Figure 15 Typical Body Diode Transfer Characteristics

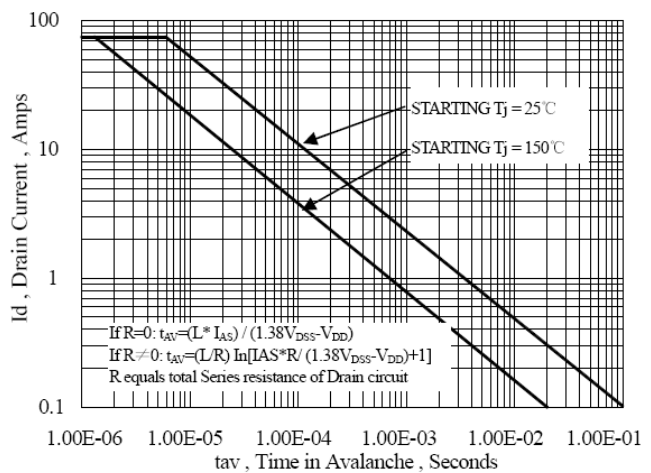


Figure 16 Unclamped Inductive Switching Capability

Company : Wuxi Guang Lei electronic technology co., LTD

TEL : 13961734102Mr.yuan

Wuxi Guang Lei electronic technology co., LTD